

Silicon NPN Power Transistors

2SC1942

DESCRIPTION

- With TO-3 package
- High breakdown voltage
- High speed switching

APPLICATIONS

- For TV horizontal output applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

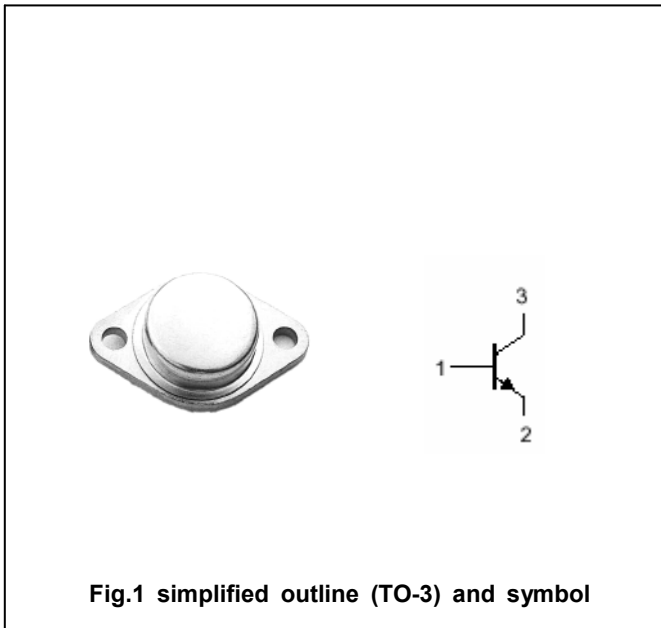


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
P _T	Total power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	2.5	°C/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5A; I _B =0.8A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.5A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =600V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =1 A ; V _{CE} =5V	8		40	

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PACKAGE OUTLINE

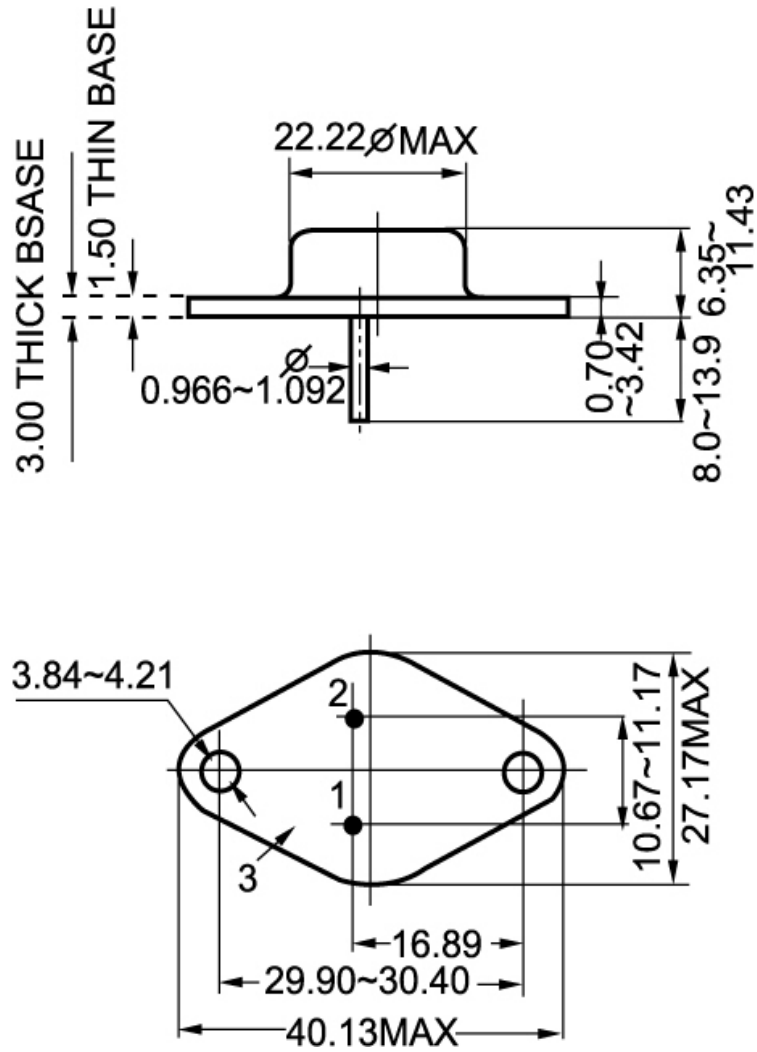


Fig.2 Outline dimensions